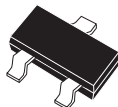


CMPT2369

NPN SILICON TRANSISTOR



SOT-23 CASE

CentralTM
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT2369 type is an NPN silicon transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for ultra high speed switching applications.

Marking Code is C1J.

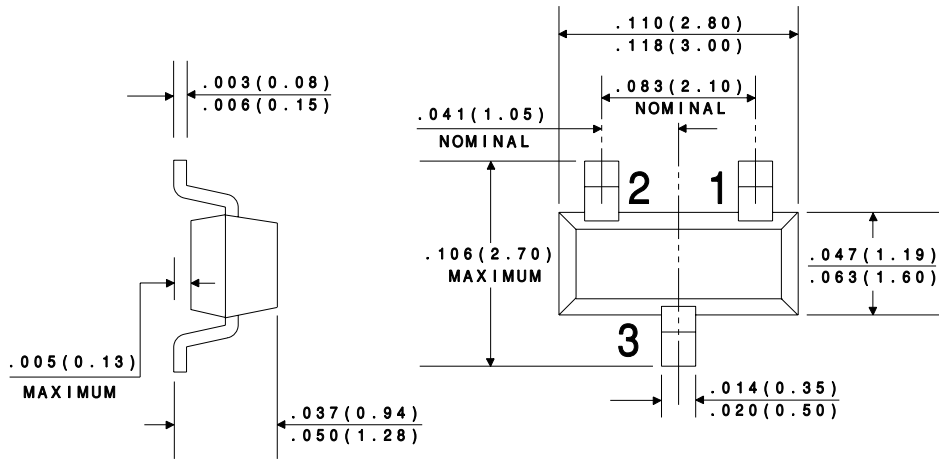
MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V _{CES}	40	V
Collector-Emitter Voltage	V _{CEO}	15	V
Emitter-Base Voltage	V _{EBO}	4.5	V
Collector Current	I _C	500	mA
Power Dissipation	P _D	350	mW
Operating and Storage			
Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	Θ _{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I _{CBO}	V _{CB} =20V		0.4	μA
I _{CBO}	V _{CB} =20V, T _A =125°C		30	μA
BV _{CBO}	I _C =10μA	40		V
BV _{CES}	I _C =10μA	40		V
BV _{CEO}	I _C =10mA	15		V
BV _{EBO}	I _E =10μA	4.5		V
V _{CE} (SAT)	I _C =10mA, I _B =1.0mA		0.25	V
V _{BE} (SAT)	I _C =10mA, I _B =1.0mA	0.7	0.85	V
h _{FE}	V _{CE} =1.0V, I _C =10mA	40	120	
h _{FE}	V _{CE} =2.0V, I _C =100mA	20		
C _{ob}	V _{CB} =5.0V, I _E =0, f=1.0MHz		4.0	pF
f _T	V _{CE} =10V, I _C =10mA, f=100MHz	500		MHz
t _s	V _{CC} =3.0V, I _C =I _{B1} =I _{B2} =10mA		13	ns
t _{on}	V _{CC} =3.0V, I _C =10mA, I _{B1} =3.0mA		12	ns
t _{off}	V _{CC} =3.0V, I _C =10mA, I _{B1} =3.0mA, I _{B2} =1.5mA		18	ns

All dimensions in inches (mm).



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR